

IPW

File No.: 14836-8US-2 AD/mb

Montreal, Canada

March 9, 2005

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In Application of:

Applicant: MICROBRIDGE TECHNOLOGIES INC.

Serial No.: 10/796,420

Filed: March 10, 2004

Title: METHOD FOR TRIMMING RESISTORS

Group Art Unit: 3742

Examiner: --

Agent of Record: Alexandra Daoud Tel: (514) 847-4333

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U.S. Patent and Trademark Office  
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Alexandria, Virginia 22313-1450  
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**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**  
**PRIOR TO FIRST OFFICE ACTION**

Sir:

Pursuant to the duty of disclosure under 37 CFR 1.56, copies of the references listed on the attached PTO Form SB08A/B are submitted herewith.

In accordance with 37 CFR 1.97(h), the submission of the present information is not to be construed as an admission that such information is, or is considered to be material to patentability.

The Examiner is kindly requested to consider these references during the examination of the above-identified application, making the references of record, and to return an initialed copy of the SB08A/B Form to the below-signed agent.

Respectfully submitted,

MICROBRIDGE TECHNOLOGIES INC.

By:



Alexandra Daoud, Registration No. 55,992  
OGILVY RENAULT  
Customer Number 020988

Enc.: Copies of references cited therein  
2 sets of SB08A/B Form

Substitute for form 1449PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
		Application Number		10/796, 420	
		Filing Date		March 10, 2004	
		First Named Inventor		Oleg GRUDIN et al.	
		Art Unit		3742	
		Examiner Name		(unknown)	
Sheet		1		of 3	
		Attorney Docket Number		14836-8US-2 AD/mb	

#U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
		Number – Kind Code <sup>2</sup> (if known)			
		US-6,097,276	Aug. 1, 2000	Van Den Broek et al.	
		US-5,844,122	Dec. 1, 1998	Kato	
		US-5,635,893	Jun. 3, 1997	Spraggins et al.	
		US-5,493,148	Feb. 20, 1996	Ohata et al.	
		US-5,460,040	Oct. 24, 1995	Tada et al.	
		US-4,902,959	Feb. 20, 1990	Brokaw	
		US-5,757,264	May 26, 1998	Petit	
		US-4,717,886	Jan. 5, 1988	Davis et al.	
		US-4,683,442	Jul. 28, 1987	Vyne	
		US-4,606,781	Aug. 19, 1986	Vyne	
		US-5,110,758	May 5, 1992	Baskett	
		US-5,563,549	Oct. 8, 1996	Shieh	
		US-			
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant Of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> – Number <sup>4</sup> – Kind Code <sup>5</sup> (if known)				
		WO 00/21196	Apr. 13, 2000	Honeywell Inc.		

Examiner Signature	Date Considered
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria VA 22313-1450.

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Sheet	2	of	3	Attorney Docket Number	14836-8US-2 AD/mb

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
		Constant Voltage Trimming of Heavily Doped Polysilicon Resistors, Japan Journal Appl. Phys. Vol. 34, Part 1, No. 1, January 1995, pp. 48-53.	
		Pulse Current Trimming of Polysilicon Resistors, Transactions of Electron Devices, IEEE, Vol. 42, N° 4, April 1995, pp. 689-695.	
		Change in Temperature Coefficient of Resistance of Heavily Doped Polysilicon Resistors Caused by Electrical Trimming, Japan Journal Appl. Phys. Vol. 35, Part 1, No. 8, August 1995, pp. 4209-4215.	
		Theory and Application of Polysilicon Resistor Trimming, Solid-State Electronics, Vol. 38, N° 11, 1995, pp. 1861-1869.	
		Electrical Trimming of Ion-Beam Sputtered Polysilicon Resistors by High Current Pulses, IEEE Transactions on Electron Devices, Vol. 41, No. 8, August 1994, pp. 1429-1434.	
		Electrical Trimming of Heavily Doped Polycrystalline Silicon Resistors, IEEE Transactions on Electron Devices, Vol. ED-26, No. 11, November 1979, pp. 738-742.	
		A Monolithic 14Bit D/A Converter Fabricated with a New Trimming Technique (DOT), IEEE, Journal of Solid-State Circuits, Vol. SC-19, N° 5, October 1984, pp. 802-807.	
		Precision Electrical Trimming of Very Low TCR Poly-SiGe Resistors, IEEE Electron Device Letters, Vol. 21, No. 6, June 2000, pp. 283-286.	
		1/f Noise Transformation that Accompanies the Trimming of Polycrystalline Silicon Layers, Solid State Phenomena, Vols. 51-52 (1996) Scitec Publications, Switzerland, pp. 391-396.	
		Micromachined Thermal Radiation Emitter from a Commercial CMOS Process, IEEE Electron Devices Letters, Vol. 12, No. 2, February 1991, pp. 57-59.	

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\*EXAMINER if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Sheet	3	of	3	Attorney Docket Number	14836-8US-2 AD/mb

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
		CMOS-Compatible High-Temperature Micro-Heater: Microstructure Release and Testing, Can. J. Elect & Comp. Eng., Vol. 25, No. 1, January 2000, pp. 002-006.	
		Reliability Study of Polysilicon for Microhotplates, 1994, Dept. of Electrical and Computer Engineering, N.R. Swart et al., University of Waterloo, Waterloo, Ont. CANADA, pp. 119-122,	
		CMOS Thermally Isolated Heater Structure as a Substrate for Semiconductor Gas Sensors, S. Wessel et al, Energy Research Institute, pp. 1.6.1 to 1.6.8.	
		A Microstructure for Measurement of Thermal Conductivity of Polysilicon Thin Films, Friedemann Völklein et al., Jour. of Microelectromechanical Systems, Vol. 1, N° 4, Dec. 1992, pp. 193-196.	
		Electrical and Optical Characteristics of Vacuum-Sealed Polysilicon Microlamps, Carlos H. Mastrangelo et al., IEEE Transactions on Electron Devices, Vol. 39, N° 6, June 1992, pp. 1363-1374.	

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